SIEMENS

Data sheet 3RF2330-1AA22



Solid-state contactor 1-phase 3RF2 AC 51 / 30 A / 40 $^{\circ}\text{C}$ 24-230 V / 110-230 V AC screw terminal

product brand name	SIRIUS
product designation	solid-state contactor
design of the product	single-phase
product type designation	3RF23
manufacturer's article number	
 1 of the accessories that can be ordered 	3RF2900-3PA88
 _4 of the accessories that can be ordered 	3RF2950-0GA33
product designation	
_1 of the accessories that can be ordered	terminal cover
_4 of the accessories that can be ordered	load monitoring
General technical data	
product function	zero-point switching
power loss [W] for rated value of the current	
• at AC in hot operating state	33 W
• at AC in hot operating state per pole	33 W
without load current share typical	3.5 W
insulation voltage rated value	600 V
degree of pollution	3
type of voltage	
 of the operating voltage 	AC
of the control supply voltage	AC
surge voltage resistance of main circuit rated value	6 kV
protection class IP	IP20
protection class IP on the front according to IEC 60529	IP20
shock resistance according to IEC 60068-2-27	15g / 11 ms
vibration resistance according to IEC 60068-2-6	2g
reference code according to IEC 81346-2	Q
Substance Prohibitance (Date)	07/01/2006
SVHC substance name	Lead - 7439-92-1 Lead monoxide (lead oxide) - 1317-36-8 Dibutylbis(pentane-2,4-dionato-O,O')tin - 22673-19-4
Weight	0.3 kg
Main circuit	
number of poles for main current circuit	1
number of NO contacts for main contacts	1
number of NC contacts for main contacts	0
type of voltage of the operating voltage	AC
operating voltage	
• at AC	
— at 50 Hz rated value	24 230 V
— at 60 Hz rated value	24 230 V

operating frequency rated value	50 60 Hz
operating range relative to the operating voltage at AC	30 00 ⊓Z
operating range relative to the operating voltage at AC	00 050 //
• at 50 Hz	20 253 V
• at 60 Hz	20 253 V
operational current	
• at AC-51 rated value	30 A
at AC-51 according to IEC 60947-4-3	22 A
according to UL 508 rated value	27 A
operational current minimum	500 mA
rate of voltage rise at the thyristor for main contacts maximum permissible	1 000 V/µs
blocking voltage at the thyristor for main contacts maximum permissible	800 V
reverse current of the thyristor	10 mA
derating temperature	40 °C
surge current resistance rated value	600 A
I2t value maximum	1 800 A ² ·s
Control circuit/ Control	
type of voltage of the control supply voltage	AC
control supply voltage 1 at AC	
• at 50 Hz	110 230 V
• at 60 Hz	110 230 V
control supply voltage frequency	
1 rated value	50 Hz
• 2 rated value	60 Hz
control supply voltage at AC	· · · ·
at 50 Hz full-scale value for signal<0> recognition	40 V
	40 V
at 60 Hz full-scale value for signal<0> recognition	40 V
control supply voltage	90 V
at AC initial value for signal <1> detection	
symmetrical line frequency tolerance	5 Hz
control current at minimum control supply voltage	
• at AC	2 mA
control current at AC rated value	15 mA
ON-delay time	40 ms; additionally max. one half-wave
OFF-delay time	40 ms; additionally max. one half-wave
Auxiliary circuit	
type of switching contact	normally open contact (NO)
number of NC contacts for auxiliary contacts	0
number of NO contacts for auxiliary contacts	0
number of CO contacts for auxiliary contacts	0
Installation/ mounting/ dimensions	
fastening method side-by-side mounting	Yes
fastening method	screw fixing and snap-on mounting on standard mounting rail 35 mm according to IEC 60715
design of the thread of the screw for securing the equipment	M4
height	95 mm
width	45 mm
depth	135.5 mm
Connections/ Terminals	
product component removable terminal for auxiliary and control circuit	Yes
type of electrical connection	
for main current circuit	screw-type terminals
for auxiliary and control circuit	screw-type terminals
type of connectable conductor cross-sections	"
• for main contacts	
— solid	2x (1.5 2.5 mm²), 2x (2.5 6 mm²)
— finely stranded with core end processing	2x (1 2.5 mm²), 2x (2.5 6 mm²), 1x 10 mm²
for AWG cables for main contacts	2x (14 10)
connectable conductor cross-section for main contacts	(·············)
Connectable conductor cross-section for main contacts	

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manufacturer's article number

- of DIAZED fuse usable
- of NEOZED fuse usable

5SB2711; These fuses have a smaller rated current than the semiconductor relays

5SE2320: These fuses have a smaller rated current than the semiconductor relays

Approvals Certificates

General Product Approval

EMV

Test Certificates











Type Test Certificates/Test Report

Test Certificates

other

Railway

Environment

Special Test Certificate

Confirmation



Special Test Certificate Environmental Confirmations

Further information

Information on the packaging

https://support.industry.siemens.com/cs/ww/en/view/109813875

Information- and Downloadcenter (Catalogs, Brochures,...)

https://www.siemens.com/ic10

Industry Mall (Online ordering system)

https://mall.industry.siemens.com/mall/en/en/Catalog/product?mlfb=3RF2330-1AA22

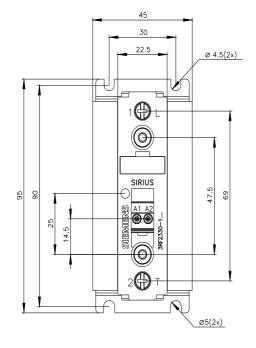
Cax online generator

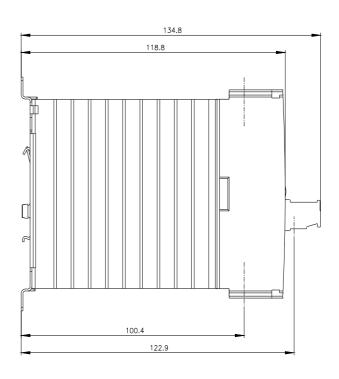
Service&Support (Manuals, Certificates, Characteristics, FAQs,...)

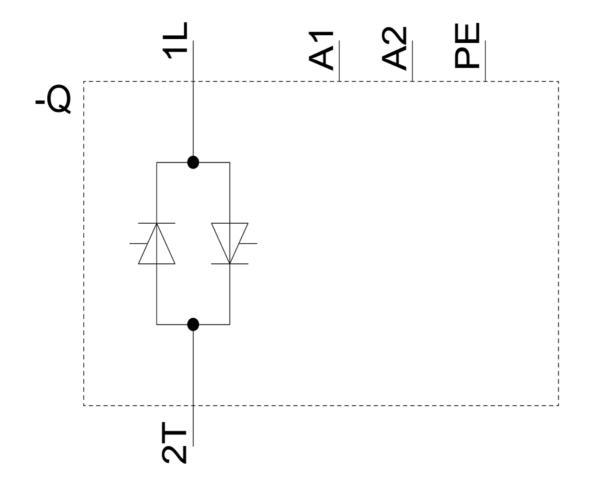
https://support.industry.siemens.com/cs/ww/en/ps/3RF2330-1AA22

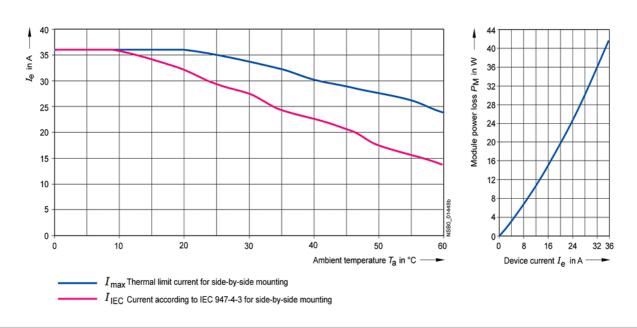
Image database (product images, 2D dimension drawings, 3D models, device circuit diagrams, EPLAN macros, ...)

http://www.automation.siemens.com/bilddb/cax_de.aspx?mlfb=3RF2330-1AA22&lang=en









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